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2815
#14/9
T. BELL
6.20.02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shunpei Yamazaki, et al. Art Unit : 2815
Serial No.: 09/302,679 Examiner : Lourdes Cruz
Filed : April 30, 1999
Title : ELECTRONIC DEVICE AND METHOD FOR MANUFACTURING THE
SAME

Commissioner for Patents
Washington, D.C. 20231

SUPPLEMENTAL AMENDMENT

Sir:

Further in response to the Official Action dated November 30, 2001, and supplemental to our Amendment filed February 27, 2002 in response to this action, please amend the above-referenced application as follows.

In the Specification:

Please replace the paragraph beginning at page 6, line 13, with the following rewritten paragraph:

--Once the silicon oxide film 103 is obtained, an aluminum film 104 is formed at a thickness of 4,000 Å by sputtering. A silicon nitride film 105 is on the aluminum film 104. Thus is obtained a state as is shown in Fig. 1A.--

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Please replace the paragraph beginning at page 7, line 16,
with the following rewritten paragraph:

G2
--The anodic oxide film 108, 109 thus obtained is dense and robust. The film thickness of the film obtained in the anodic oxidation step can be controlled by adjusting the applied voltage.--

Please replace the paragraph beginning at page 15, line 24,
with the following rewritten paragraph:

G3
--Then, a 2000-Å-thick silicon nitride film is formed by plasma CVD to provide a first interlayer insulating film 616, and a polyimide film is formed thereafter to obtain a second interlayer insulating film 613. The structure thus obtained is shown in Fig. 7A.--

In the Claims:

Please amend the claims as follows.

42. (Amended) A display device comprising:

a substrate;

G4
a thin film transistor over said substrate, said thin film transistor having a source region, a drain region, a channel region between said source and drain region, a gate electrode over said channel region;

an interlayer insulating film over said thin film transistor;

34' control
a wiring connected to said source or drain region through a contact hole; and

a pixel electrode over said interlayer insulating film, wherein said gate electrode and wiring are formed from a film comprising aluminum, and

wherein said film contains carbon atoms at a concentration of 5×10^{18} atoms·cm⁻³ or less and nitrogen atoms at a concentration of 7×10^{17} atoms·cm⁻³ or less.

35
49. A display device according to claim 12, said display device is an electroluminescence display device.

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85. A display device according to claim 42, wherein said display device is an electroluminescence display device.

REMARKS

Reconsideration and allowance of the above-referenced application are respectfully requested.

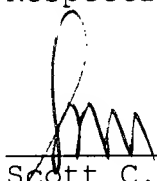
Applicants herewith correct some informal errors occurring in the drawings and also correct some issues in the specification. No new matter is introduced by this current amendment.

Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: _____

5/14/02



Scott C. Harris
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SCH/smr

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